

GaAs INTEGRATED CIRCUIT μ PG2250T5N

1.8 V, POWER AMPLIFIER FOR Bluetooth™ Class 1

DESCRIPTION

The LtPG2250T5N is a GaAs MMIC for power amplifier which was developed for Bluetooth Class 1.

This device realizes high efficiency, high gain and high output power.

This device is housed in a 6-pin plastic TSON (<u>Thin Small Out-line Non-leaded</u>) package. And this package is able to high-density surface mounting.

FEATURES

Operating frequency : f_{opt} = 2 400 to 2 500 MHz (2 450 MHz TYP.)
 Supply voltage : V_{DD}1, 2, 3 = 1.5 to 3.5 V (1.8 V TYP.)

Control voltage : V_{cont} = 1.5 to 2.1 V (1.8 V TYP.)

Circuit current
 : IDD = 100 mA TYP. @ VDD1, 2, 3 = 1.8 V, Vcont = 1.8 V, Pout = +19 dBm

: IDD = 170 mA TYP. @ VDD1, 2, 3 = 3.0 V, Vcont = 1.8 V, Pout = +24 dBm

• Output power : Pout = +20.0 dBm TYP. @ VDD1, 2, 3 = 1.8 V, Vcont = 1.8 V, Pin = -5 dBm

: Pout = +25.0 dBm TYP. @ VDD1, 2, 3 = 3.0 V, Vcont = 1.8 V, Pin = -5 dBm

• Gain control range : GCR = 60 dB TYP. @ VDD1, 2, 3 = 1.8 V, Vcont = 0 to 1.8 V, Pin = -5 dBm

High efficiency : PAE = 55% TYP. @ VDD1, 2, 3 = 1.8 V, Vcont = 1.8 V, Pin = -5 dBm

• High-density surface mounting : 6-pin plastic TSON package (1.5 \times 1.5 \times 0.37 mm)

APPLICATION

Power Amplifier for Bluetooth Class 1

ORDERING INFORMATION

Part	Number	Order Number	Package	Marking	Supplying Form
μPG22	50T5N-E2	μPG2250T5N-E2-A	6-pin plastic TSON (Pb-Free)	G5C	Embossed tape 8 mm wide Pin 1, 6 face the perforation side of the tape Qty 3 kpcs/reel

Remark To order evaluation samples, contact your nearby sales office.

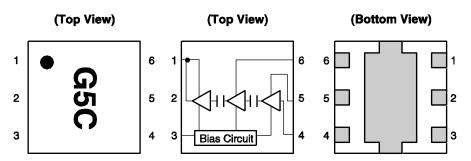
Part number for sample order: μ PG2250T5N-A

Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

Document No. PG10639EJ03V0DS (3rd edition) Date Published February 2008 NS

PIN CONNECTIONS AND INTERNAL BLOCK DIAGRAM



Pin No.	Pin Name		
1	OUTPUT/V _{DD} 3		
2	N.C.		
3	Vcont		
4	INPUT		
5	V _{DD} 1		
6	V _{DD} 2		

Remark Exposed pad: GND

ABSOLUTE MAXIMUM RATINGS (TA = +25°C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Supply Voltage	V _{DD} 1, 2, 3	5.0	V
Control Voltage	Vcont	2.4	V
Circuit Current	I _{DD}	250	mA
Control Current	Icont	5	mA
Input Power	Pin	+5	dBm
Power Dissipation	PD	400 Note	mW
Operating Ambient Temperature	TA	-40 to +85	°C
Storage Temperature	Tstg	-55 to +150	°C

Note Mounted on double-sided copper-clad $50 \times 50 \times 1.6$ mm epoxy glass PWB, $T_A = +85^{\circ}C$

RECOMMENDED OPERATING RANGE (TA = +25°C, unless otherwise specified)

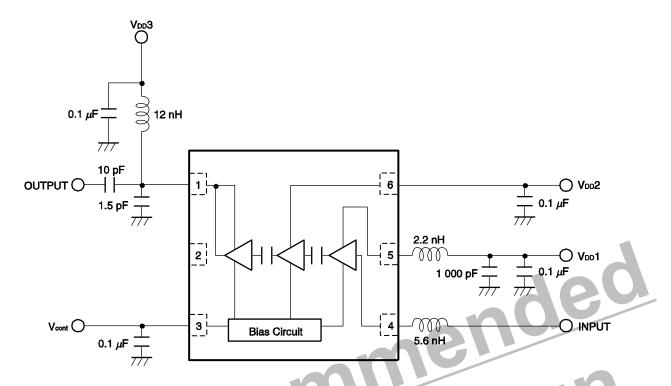
Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Operating Frequency	fopt	2 400	2 450	2 500	MHz
Supply Voltage	V _{DD} 1, 2, 3	1.5	1.8	3.5	V
Control Voltage	V _{cont}	1.5	1.8	2.1	V

ELECTRICAL CHARACTERISTICS (TA = +25°C, VDD1, 2, 3 = 1.8 V, Vcont = 1.8 V, f = 2 450 MHz, external input and output matching, unless otherwise specified)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current	IDD	Pout = +19 dBm	-	100	130	mA
		Vpd1,2,3 = 3.0 V, Pout = +24 dBm	_	170	-	mA
Control Current	Icont	Pout = +19 dBm	-	-	3	mA
Shut Down Current	Ishut down	V _{cont} = 0 V, RF None	-	-	5	μΑ
Output Power 1	Pout1	Pin = -5 dBm	+19	+20	-	dBm
		V _{DD} 1,2,3 = 3.0 V, P _{in} = −5 dBm	-	+25	-	dBm
Output Power 2	Pout2	V _{cont} = 0 V, P _{in} = -5 dBm	_	-40	-	dBm
Gain Control Range	GCR	V _{cont} = 0 to 1.8 V, P _{in} = -5 dBm	_	60	-	dB
Efficiency	PAE	Pin = -5 dBm	-	55	-	%
2nd Harmonics	2f0	Pin = -5 dBm	_	35	_	dBc

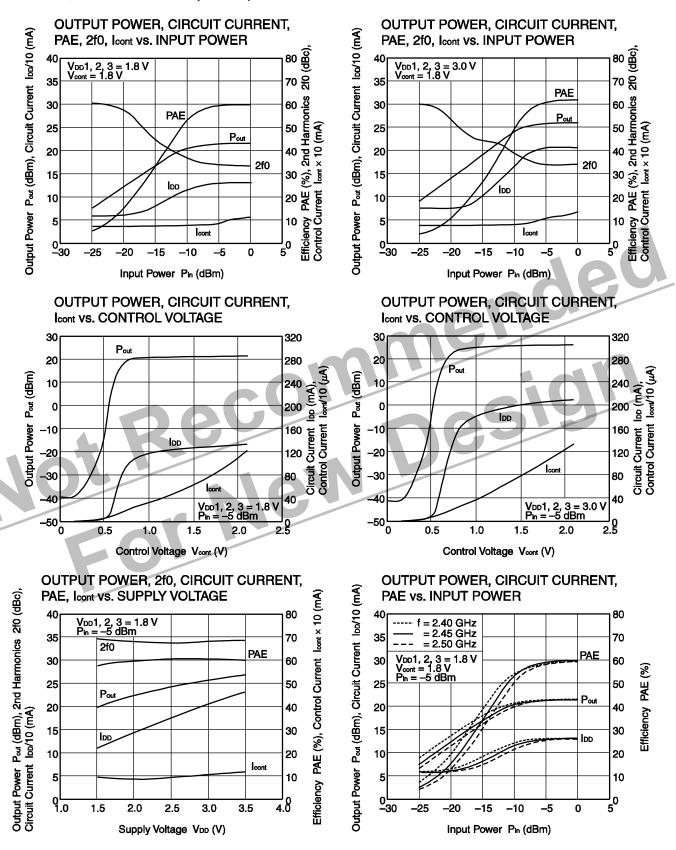


EVALUATION CIRCUIT



The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

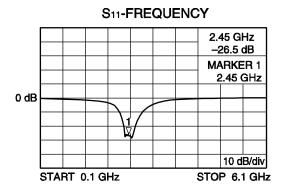
TYPICAL CHARACTERISTICS ($T_A = +25$ °C, f = 2450 MHz, with external input and output matching circuits, unless otherwise specified)

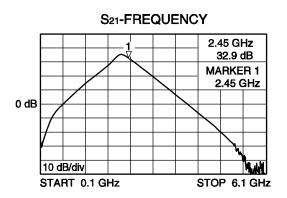


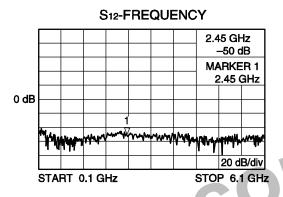
Remark The graphs indicate nominal characteristics.

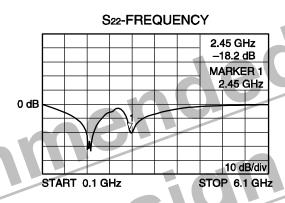
S-PARAMETERS 1

Condition: f = 0.1 to 6.1 GHz, $P_{in} = -30 \text{ dBm}$, $V_{cont} = 1.8 \text{ V}$, $V_{DD}1 = V_{DD}2 = V_{DD}3 = 1.8 \text{ V}$



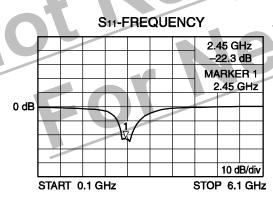


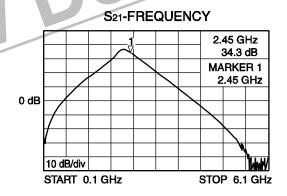


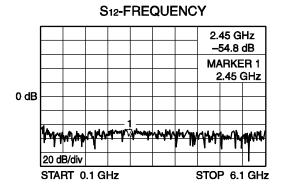


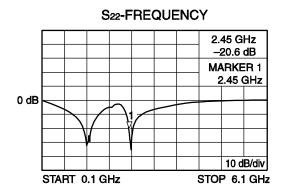
S-PARAMETERS 2

Condition : f = 0.1 to 6.1 GHz, $P_{in} = -30$ dBm, $V_{cont} = 1.8$ V, $V_{DD}1 = V_{DD}2 = V_{DD}3 = 3.0$ V







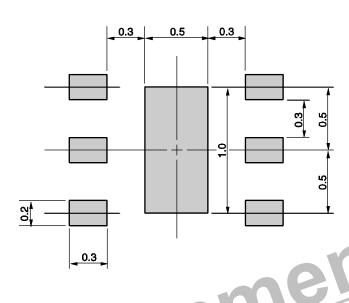


Remark The graphs indicate nominal characteristics.

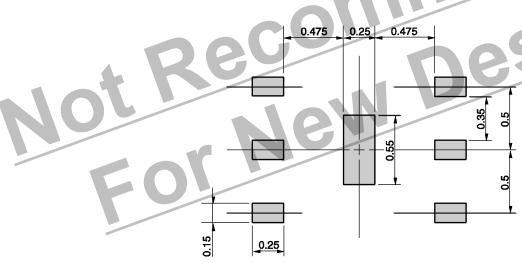
MOUNTING PAD AND SOLDER MASK LAYOUT DIMENSIONS

6-PIN PLASTIC TSON (UNIT: mm)

MOUNTING PAD



SOLDER MASK

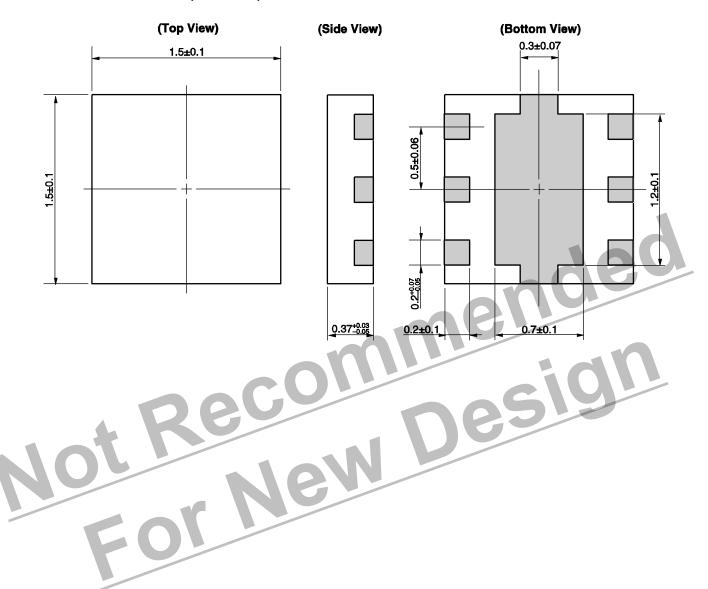


Solder thickness: 0.08 mm

Remark The mounting pad and solder mask layouts in this document are for reference only.

<R> PACKAGE DIMENSIONS

6-PIN PLASTIC TSON (UNIT: mm)



RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds	IR260
	Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 3 times : 0.2%(Wt.) or below	
Wave Soldering	Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (terminal temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).



Caution

GaAs Products

This product uses gallium arsenide (GaAs).

GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.

- Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.
 - Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.
 - 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.
- Do not burn, destroy, cut, crush, or chemically dissolve the product.
- Do not lick the product or in any way allow it to enter the mouth.



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